

Philips

Diode PBYR2045CTB

Datasheet

Schottky Dual Diode

PBYR2045CTB

45V / 20A

DATASHEET

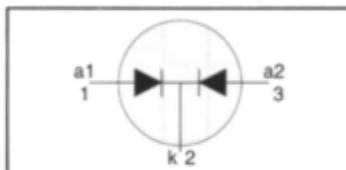
OEM – Philips

Source: Philips Databook 1999

Datasheet Rev. 1.3 – 04/19 – data without warranty / liability

**Rectifier diodes
Schottky barrier**
PBYR2045CT, PBYR2045CTB series
FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

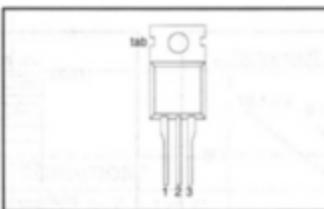
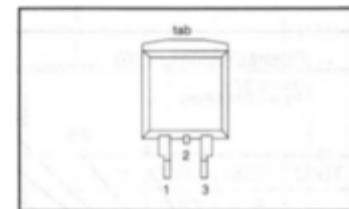
SYMBOL**QUICK REFERENCE DATA** $V_R = 40 \text{ V} / 45 \text{ V}$ $I_{O(AV)} = 20 \text{ A}$ $V_F \leq 0.57 \text{ V}$ **GENERAL DESCRIPTION**

Dual, common cathode schottky rectifier diodes in a conventional leaded plastic package and a surface mounting plastic package. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR2045CT series is supplied in the SOT78 conventional leaded package.
The PBYR2045CTB series is supplied in the SOT404 surface mounting package.

PINNING

PIN	DESCRIPTION
1	anode 1 (a)
2	cathode (k) ¹
3	anode 2 (a)
tab	cathode (k)

SOT78 (TO220AB)**SOT404****LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	PBYR20 PBYR20	MIN.		UNIT
				40CT	45CT	
V_{RRM}	Peak repetitive reverse voltage		-	40	45	V
V_{RWM}	Working peak reverse voltage		-	40	45	V
V_R	Continuous reverse voltage	$T_{mb} \leq 106 \text{ }^\circ\text{C}$	-	40	45	V
$I_{O(AV)}$	Average rectified forward current (both diodes conducting)	square wave; $\delta = 0.5$; $T_{mb} \leq 128 \text{ }^\circ\text{C}$	-	20		A
I_{FRM}	Repetitive peak forward current per diode	square wave; $\delta = 0.5$; $T_{mb} \leq 128 \text{ }^\circ\text{C}$	-	20		A
I_{FSM}	Non-repetitive peak forward current per diode	$t = 10 \text{ ms}$ $t = 8.3 \text{ ms}$	-	135		A
		sinusoidal; $T_j = 125 \text{ }^\circ\text{C}$ prior to surge; with reapplied $V_{RRM(max)}$ pulse width and repetition rate limited by $T_{j,max}$	-	150		A
I_{RRM}	Peak repetitive reverse surge current per diode		-	1		A
T_j	Operating junction temperature		-	150		$^\circ\text{C}$
T_{stg}	Storage temperature		-65	175		$^\circ\text{C}$

1. It is not possible to make connection to pin 2 of the SOT404 package.

Rectifier diodes
Schottky barrier

PBYR2045CT, PBYR2045CTB series

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	per diode	-	-	2	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	both diodes SOT78 package in free air SOT404 package, pcb mounted, minimum footprint, FR4 board	-	60	-	K/W
			-	50	-	K/W

ELECTRICAL CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	Forward voltage per diode	$I_F = 10 \text{ A}; T_j = 125^\circ\text{C}$ $I_F = 20 \text{ A}; T_j = 125^\circ\text{C}$ $I_F = 20 \text{ A}$	-	0.45	0.57	V
I_R	Reverse current per diode	$V_R = V_{RWM}$ $V_R = V_{RWM}; T_j = 100^\circ\text{C}$ $V_R = 5 \text{ V}; f = 1 \text{ MHz}, T_j = 25^\circ\text{C} \text{ to } 125^\circ\text{C}$	-	0.64	0.72	V
C_d	Junction capacitance per diode	-	0.64	0.84	1.3	mA
		-	0.3	22	35	mA
		-	380	-	-	pF

**Rectifier diodes
Schottky barrier**

PBYR2045CT, PBYR2045CTB series

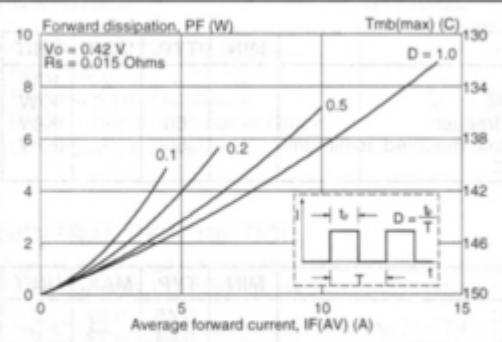


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

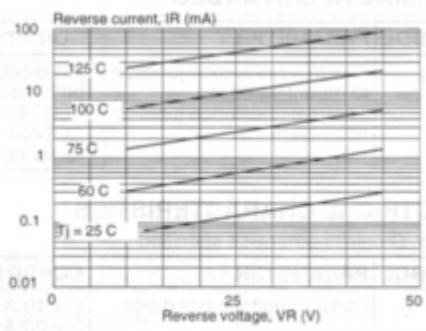


Fig.4. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_J

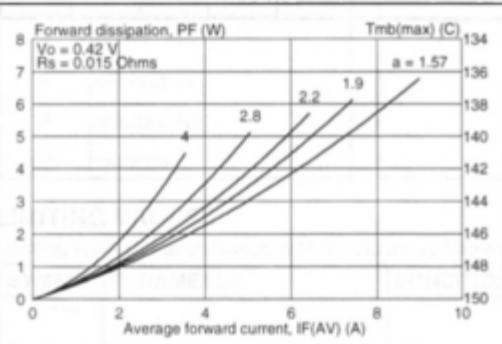


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where $a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$.

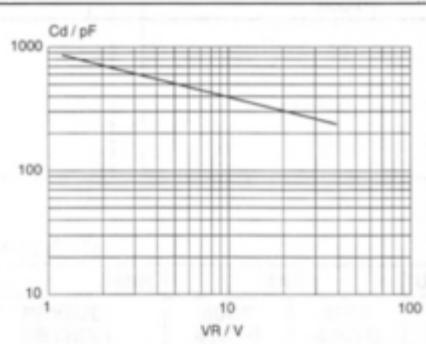


Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; $f = 1\text{ MHz}$; $T_J = 25^\circ\text{C}$ to 125°C .

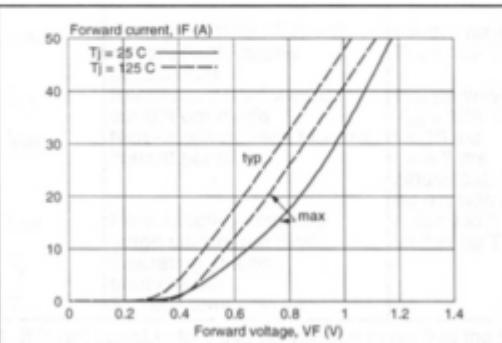


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_J

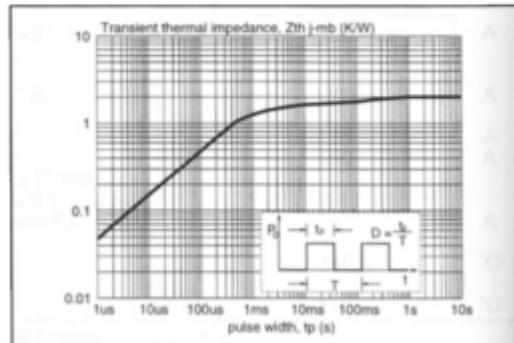


Fig.6. Transient thermal impedance per diode; $Z_{th(j-mb)} = f(t_p)$.